## **Analog Power**

## P-Channel 40-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low  $r_{DS(on)}$  and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, cellular and cordless telephones.

- Low r<sub>DS(on)</sub> provides higher efficiency and extends battery life
- Low thermal impedance copper leadframe DFN3x3-8PP saves board space
- Fast switching speed
- High performance trench technology

PRODU	JCT S	UMMA	RY			
V <sub>DS</sub> (V)		r <sub>DS(on)</sub>	ID	<b>)</b> (A)		
-40	12	2 @ V <sub>G</sub>	$_{\rm S} = -10 {\rm V}$	-	-14	
-40	18	$18 @ V_{GS} = -4.5V$			-12	
	S □ S □ S □ G □		3x3-8PP 5 View 8 7 6 5		G o	
		ļ			P-Channel I	MOSE

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C UNLESS OTHERWISE NOTED)						
Parame te r	Symbol	Maximum	Units			
Drain-Source Voltage			-40	v		
Gate-Source Voltage	V <sub>GS</sub>	±20	v			
Continuous Drain Current <sup>a</sup>	$T_A=25^{\circ}C$		-14			
Continuous Drain Current	$T_{A}=25^{\circ}C$ $T_{A}=70^{\circ}C$	ID	-12	А		
Pulsed Drain Current <sup>b</sup>	I <sub>DM</sub>	±50				
Continuous Source Current (Diode Conduction) <sup>a</sup>	Is	-2.1	А			
Deriver Dissingtion <sup>a</sup>	$T_{A}=25^{\circ}C$ $T_{A}=70^{\circ}C$	D.,	3.5	w		
Power Dissipation <sup>a</sup>	$T_A=70^{\circ}C$	гD	2.0	**		
Operating Junction and Storage Temperature Range	TJ, Tstg	-55 to 150	°C			

THERMAL RESISTANCE RATINGS							
Parameter	Symbol	Maximm	Units				
a a a a a a	t <= 10 sec	D	35	°C/W			
Maximum Junction-to-Ambient <sup>a</sup>	Steady State	R <sub>0JA</sub>	81	°C/W			

Notes

a. Surface Mounted on 1" x 1" FR4 Board.

b. Pulse width limited by maximum junction temperature

SPECIFICATIONS (T <sub>A</sub> = $25^{\circ}$ C UNLESS OTHERWISE NOTED)								
Parameter	Symbol	Test Conditions	Limits			Unit		
i arameter	Symbol			Тур	Max	Unit		
Static								
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250 \text{ uA}$	-1			V		
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V},  V_{GS} = \pm 20 \text{ V}$			±100	nA		
Zero Gate Voltage Drain Current		$V_{DS}$ = -32 V, $V_{GS}$ = 0 V			-1	uA		
Zelo Gale Voltage Dialit Current	I <sub>DSS</sub>	$V_{DS}$ = -32 V, $V_{GS}$ = 0 V, $T_{J}$ = 55°C			-5	UA		
On-State Drain Current <sup>A</sup>	I <sub>D(on)</sub>	$V_{DS}$ = -5 V, $V_{GS}$ = -10 V	-50			Α		
Drain-Source On-Resistance <sup>A</sup>	r <sub>z o</sub> ( )	$V_{GS}$ = -10 V, $I_{D}$ = -1 A			12	mΩ		
	r <sub>DS(on)</sub>	$V_{GS}$ = -4.5 V, $I_D$ = -1 A			18			
Forward Tranconductance <sup>A</sup>	g <sub>fs</sub>	$V_{DS} = -15 V, I_{D} = -1 A$		29		S		
Diode Forward Voltage	V <sub>SD</sub>	$I_{\rm S}$ = 1 A, $V_{\rm GS}$ = 0 V		-0.8		V		
Dynamic <sup>b</sup>								
Total Gate Charge	Qg	V <sub>DS</sub> = -15 V, V <sub>GS</sub> = -5 V,		50		nC		
Gate-Source Charge	Q <sub>gs</sub>	v <sub>DS</sub> = -15 v, v <sub>GS</sub> = -5 v, I <sub>D</sub> = -1 A		10				
Gate-Drain Charge	Q <sub>gd</sub>	$I_D = -I A$		10				
Turn-On Delay Time	t <sub>d(on)</sub>			9				
Rise Time	tr	$V_{DD}$ = -15 V, $R_L$ = 6 $\Omega$ ,		10		nS		
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_{D} = -1 A, V_{GEN} = -10 V$		100				
Fall-Time	t <sub>f</sub>			40		1		

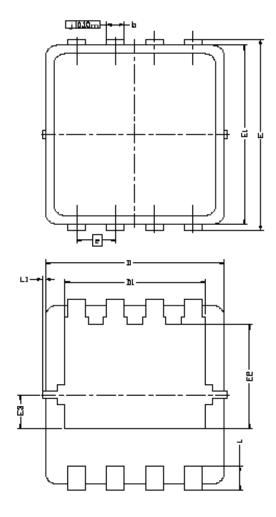
Notes

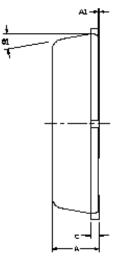
a. Pulse test:  $PW \le 300$ us duty cycle  $\le 2\%$ .

b. Guaranteed by design, not subject to production testing.

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## Package Information





TIM	MILLIMETERS			INCHES				
DIM.	MIN	NDM	MAX	MIN	NDM	MAX		
A	0,700	0,80	0.900	0.0276	0.0315	0,0354		
A1	0.00		0.05	0.000		0.002		
b	0.24	0.30	0.35	0.009	0.012	0.014		
C	0,10	0.152	0,25	0,004	0,006	0,010		
ם	63	28 00.8S	C	0.118 BSC				
D1	tu tu	.35 BS	С	0.093 BSC				
Ε	3	1,20 BS	С	0,	126 BSC			
E1	3.00 BSC 0.118 BSC					:C		
E5	1	1.75 BSC 0.069 BSC				C		
E3	0.575 BSC			0.023 BSC				
6	Ó	0.65 BSC			0.026 BSC			
L	0,30	0,40	0,50	0,0118	0.0157	0.0197		
L1			0.100	D		0.004		
<b>0</b> 1	Û°	10*	12*	Ū*	10°	12°		